PCCP

Accepted Manuscript

This is an *Accepted Manuscript*, which has been through the Royal Society of Chemistry peer review process and has been accepted for publication.

Accepted Manuscripts are published online shortly after acceptance, before technical editing, formatting and proof reading. Using this free service, authors can make their results available to the community, in citable form, before we publish the edited article. We will replace this *Accepted Manuscript* with the edited and formatted *Advance Article* as soon as it is available.

You can find more information about *Accepted Manuscripts* in the [Information for Authors](http://www.rsc.org/Publishing/Journals/guidelines/AuthorGuidelines/JournalPolicy/accepted_manuscripts.asp).

Please note that technical editing may introduce minor changes to the text and/or graphics, which may alter content. The journal's standard [Terms & Conditions](http://www.rsc.org/help/termsconditions.asp) and the **Ethical guidelines** still apply. In no event shall the Royal Society of Chemistry be held responsible for any errors or omissions in this *Accepted Manuscript* or any consequences arising from the use of any information it contains.

www.rsc.org/pccp

Cite this: DOI: 10.1039/c0xx00000x

www.rsc.org/xxxxxx

ARTICLE TYPE

A Synergy Effect of Sodium on the Phase Transition of Tungsten-doped Vanadium Dioxide

Qiang Song*^a***, Weitao Gong***^a***, Guiling Ning****^a* **, Hassan Mehdi***^a***, Guiqi Zhang***^a***, Junwei Ye***^a***and Yuan Lin***^a*

Received (in XXX, XXX) Xth XXXXXXXXX 20XX, Accepted Xth XXXXXXXXX 20XX ⁵**DOI: 10.1039/b000000x**

A synergy effect of sodium on the metal-insulator transition temperature reduction of tungsten doped vanadium dioxide is noted. With the assistance of sodium, doping with tungsten yields an extra depression in the phase temperature of 6-12°C ¹⁰**over that of 20-26°C per at% of tungsten.**

Vanadium dioxide (VO_2) , owing to its inherent insulatormetal transitions (MIT) properties¹, has draw continuous attention as a remarkable candidate for "smart" optical and electrical materials, such as thermochromic coatings and temperature-15 sensing switchings.² However, the critical temperature (T_C) of its MIT at $~67^{\circ}$ C restricts its further applications in those fields, which usually require the regulation of T_C over a wider range, especially to room temperature efficiently. Amongst several strategies (doping, stress and finite size) to regulate the T_c for

- 20 VO_2 MIT, doping with some donor impurity atoms is the most effective and readily realized. In particular, substitutional doping of the vanadium (V) with tungsten (W) is the most prominent, which yields a reduction of T_c in the phase transition by \sim 20 to 26 °C per at% of W.³ The reason was proved to originate from
- $_{25}$ the charge transfer from W ions to V weakens the V-V pairs.⁴ In our earlier work, W-doped vanadium dioxide have been successfully synthesized by thermal reduction and annealing.⁵ However, it always requires relative high dose of W dopants to realize efficient reduction of $T_{\rm C}$ at room temperature. In this case,
- ³⁰more structural distortion and impurities are brought to impact materials performance negatively.^{6,7} To solve this problem, codoping with W and other elements, has been investigated recently.⁸ Such as, Co-doping with W and Mo showed a superior property in lowering phase transition temperature, and W-F and
- 35 W-Ti co-doped VO₂ having better infra-red transmittance and electrical resistivity.⁹ Tang et al. discovered a charge compensation between W ion and V ion due to replacing the V^{4+} sublattice with W^{6+} in VO_2 system. Nevertheless, alkali elements (such as sodium) never have been considered as co-doping of the
- 40 VO₂ with W, although alkali metals have been widely used considering their capability of charge compensation on rare earth doped phosphor materials, which generally induce the enhancement of the intensity of the luminescence.¹⁰ Therefore, it is feasible that the charge transfer of W doped $VO₂$ system would
- ⁴⁵be influenced via co-doping with sodium, and some worthwhile results would be expected. In this communication, we present our results to show the reduction of T_c of VO_2 induced by W and sodium co-doping.

Herein we have tried to use sodium tungstate $(Na₂WO₄)$ as ⁵⁰the full dopant that both sodium (Na) and W elements could be introduced into the final product via high temperature melt and thermal reduction. This is not possible for several reported approaches, such as hydrothermal synthesis and thermolysis, where sodium ions were generally removed during washing

55 step.^{5, 6} Notably, it is found that $Na₂WO₄$ as a dopant makes doping the V sublattice with W lower the phase transition temperature more efficiently. This is the first time Na metal used as co-doping for W-doped $VO₂$, which plays a vital role in the process of the phase transition.

 60 Doped VO₂ powders were characterized via X-ray diffraction (XRD). The XRD patterns of doped $VO₂$ with various extents of Na2WO⁴ are depicted in Figure 1(a). All of the main diffraction peaks can be indexed to monoclinic $VO₂ (M1)$ (space group: *P21/c*, *a*=5.752 Å, *b*=4.538 Å, *c*=5.383Å, Joint Committee on ⁶⁵Powder Diffraction Standards (JCPDS) No. 043-1051). The strong intensity of the (011) points to the preferential growth direction of these crystal structures, as noted formerly for $VO₂$ materials prepared by solvothermal, thermolysis, etc. $5,11$ From the detail of XRD patterns, with increasing the adding amount of $70 \text{ Na}_2\text{WO}_4$, the 2 θ value of the most prominent reflection was shifted from the (011) plane of M1 down to the (110) reflections attributed to the R phase (space group: *P42/mnm*, *a*=4.554 Å, $c=2.855\text{\AA}$, JCPDS No. 044-0253), as depicted in figure 1(b). As shown in Figure 1(b), the rutile phase has been observed in the τ ₇₅ samples doped with high amount of Na₂WO₄ (more than 1 at. %) at room temperature. Raman spectroscopy analysis (Figure S1 ESI†) confirm further the stabilization of the rutile phase at room temperature. Additionally, there is no any diffraction peaks assigned to other vanadium compound or tungsten compound in ⁸⁰XRD patterns of all the samples. This result indicates that there is no any foreign crystalline phase matter in this doping process. The characteristic diffraction peaks of the XRD patterns shown in the Figure S2 ESI† are assignable to the monoclinic phase for undoped, doped $VO₂$ samples with other dopants were 85 synthesized by the same approach, suggesting as a monoclinic structure

Figure 1 (a) X-ray diffraction pattern measured at room temperature for doped VO_2 samples with different Na_2WO_4 addition. (b) A magnified ⁵version of the XRD data with different Na2WO4 doping contents in the27.0°≤2θ≤28.5°range. The vertical lines indicate the (011) peak positions expected for monoclinic VO2 from JCPDS Card no. 043-1051.

- In order to investigate the detailed compositions of doping VO² powders, X-ray photoelectron spectroscopy (XPS) 10 measurements were performed. Figure 2 shows the XPS pattern of the 1.5 at.% $Na₂WO₄$ doped $VO₂$ sample synthesized by our ammonia reduction scheme. F According to the spectra in Figure 2(a), elements, such as carbon, vanadium, oxygen, tungsten and sodium are observed where the carbon may be attributed to ¹⁵ surface contamination.¹² while the peaks assigned to W_{4f} and Na_{1s} are quite weak due to the low doping content. On the other hand, vanadium, oxygen and tungsten are studied by fitting the highresolution XPS spectra of V_{2p} , O_{1s} and W_{4f} respectively. The peaks are shown as in Figure 2(b), at 517.4eV and 516.0eV are 20 associated with $V_{2p3/2}$, and the peaks at 524.8eV and 523.1eV are assigned to $V_{2p1/2}$. According to the spectra, two clear vanadium valence (V^{4+} and V^{5+}) states are observed due to the oxidation of V^{4+} on the surface of the sample.¹² The result of O_{1s} has been shown in figure 1(c). The binding energy at 530.1 eV attributed 25 to VO_x . While the other two peaks located at higher binding energies (around 531.8 and 533.9 eV) are attributed to OH or
- H2O. In Figure 2(d)**,** the peaks at 37.1eV and 35.0 eV are attributed to $W^{6+}_{4f5/2}$ and $W^{6+}_{4f7/2}$,¹³ separately, indicating the valence of W^{6+} in the doped VO_2 powder, which is in agreement 30 with the result of Tang et al.¹⁰

Figure 2 X-ray photoelectron spectroscopy pattern of 1.5at% of Na₂WO₄ doped $VO₂$ sample: (a) wide scan spectra, high-resolution XPS profiles of (b) V_{2p} , (c) O_{1s} and (d) W_{4f} for 1.5at% of Na₂WO₄ doped VO₂.

 35 The phase transition temperature of doped $VO₂$ with different extents of $Na₂WO₄$ using is evidenced by the differential scanning calorimetry (DSC) curves shown in Figure 3(a). It indicates that the T_c for the monoclinic \rightarrow tetragonal transition is reduced from 49.0 to 4.3°C, with increasing the concentration of 40 Na₂WO₄ from 0.5% to 2.0 %, the linear fitting curve is obtained as shown in Figure 3(b) giving rising to the reduction efficiency is about 32°C per at% of W. This result an excellent among reported data.

⁴⁵**Figure 3** (a) DSC curves of doped VO2 samples with different amount of Na₂WO₄; (b) Relationship between Na₂WO₄ adding level and the phase transition temperature of $VO₂$; (c) DSC curves of doped $VO₂$ sample with 1 at% WO3 added and VO2 sample doping with 2at.% NaOH and 1 at% WO₃ successively; (d) DSC curve of the 1.0 at.% Na₂WO₄ doped and 1.0 50 at.% WO₃ doped VO₂ samples have been annealed in N₂ at 700 °C for 5h, and further annealed in N_2 at 1100 °C for 2h.

As a comparison, the sample doping with WO_3 exhibits quite different results shown in Figure 3(c) for $1at.$ % WO₃ doping sample. The MIT was only shifted down to \sim 37.3°C in the ⁵⁵heating cycle, which was about 6°C higher than doping with 1 at.% Na₂WO₄. On the other hand, VO₂ samples with only doping sodium hydroxide (NaOH) showed similar thermal behaviour compared with pure $VO₂$ sample (Figure S3 ESI†),

indicating the single element of Na barely affects the phase transition temperatures. Interestingly, the sample, doped successively with $2at$.% NaOH and 1 at% WO_3 , shows a peak attributable to the phase transition at∼30.9 °C during the ⁵heating cycles, which is equivalent with the effect of doped

- with 1at.% Na₂WO₄. Accordingly, all above results demonstrated that Na dopant play a role to facilitate the effect of W doped in the phase transition of VO_2 .
- To further exploring how Na dopant affects the MIT 10 properties, the existing state of Na ions in samples is the key problem. In this case, XRD patterns for V_2O_5 precursors obtained upon the fusion of V_2O_5 with different tungsten doping agents are firstly explored (Figure S4 ESI†). It is found that no segregated WO_x phases are detected in doped $V₂O₅$ precursor. However, it ¹⁵exhibits three characteristic diffraction peaks (asterisks)
- assignable to the monoclinic phase of $Na_{0.33}V₂O₅$ (JCPDS-48-0382) for the sample doping with 1 at% $Na₂WO₄$, suggesting that Na ions just intercalate into layers of V_2O_5 precursors not replacing V as W atom did. 14 Moreover, only diffraction peaks
- $_{20}$ corresponding to the phases of $\rm VO_2$ are observed in XRD patterns of all doped $VO₂$ samples, suggestive of the formation of homogeneous solid-solutions. Similarly, only diffraction peaks corresponding to the phases of $VO₂$ is observed in XRD patterns of sample which has been obtained by reduction of Na_2WO_4
- 25 doped V_2O_5 precursor, suggestive of the formation of homogeneous solid-solutions. It indicates Na atoms may be interstitial atoms in $VO₂$ solid-solution, which could be existed in lattice defects or interstitial positions near W atoms rather than replace V sites.
- ³⁰Meanwhile, the energy dispersion spectroscopy (EDS) results have revealed the surface composition of the $VO₂$ samples with a addition of 1at.% Na_2WO_4 (Figure 4). It is strong evidence about the presence of metal elements of W, V, and Na in the particle surface and the detailed data are summarized in Table 1. The
- ³⁵contents of Na and W are determined to be 2.58 and 1.35 at% respectively, which are somewhat more effective result than the actually data, because small quantities of $Na₂WO₄$ impurity atoms (including Na and W) did not locate in the lattice, deposition occur in the particle surface. Particularly under high
- ⁴⁰temperature annealing, a noticeable shift of surface composition is recorded on the doped $VO₂$ particle surface, together with changing the morphology from nano-aggregates to bulk shown in Figure4 (c) and (d). It shows that huge quantities of Na atoms and small amounts of W atoms migrated from inside to the surface of
- 45 the doped $VO₂$ particles during thermal treatment processing. Furthermore, as shown in Figure 3(d), after high temperature annealing treatment, the phase transition temperature shift up to ~46.8°C which is close to the T_C of 1 at.% WO₃ doped VO₂. This result clearly indicates that the effect of Na in W doped $VO₂$ for
- 50 the temperature of MIT depressed due to the migration of Na atoms at high temperature. It also proved that doping with $Na₂WO₄$ can get extra reduction in the phase temperature due to the effect of Na atoms in W-doped $VO₂$. Figure 5 shows a credible mechanism of the atomic migration of doped $VO₂$ in ₅₅ high temperature annealing.

Table 1 Metal atoms compositions of 1.0at.% $Na₂WO₄$ doped $VO₂$ sample: (a) annealed in N_2 at 700 °C for 5h, (b) further annealed in N_2 at 1100 °C for 2h

Figure 4 EDS spectrum of 1.0at.% Na₂WO₄ doped VO₂ samples: (a) annealed in N₂ at 700 °C for 5h, (b) further annealed in N₂ at 1100 °C for 2h; SEM images of $1.0at$ % Na₂WO₄ doped VO₂ samples (c) have been annealed in N₂ at 700 °C for 5h and (d)further annealed in N₂ at 1100 °C ⁶⁵for 2h**.**

Figure 5 Schematic of ions motivation at high temperature annealing for $Na₂WO₄$ doping $VO₂$ powder

With above results in hand, we can deduce preliminarily the 70 plausible mechanism. In the relevant literatures, it has been established that a charge transfer occurs and results in the pile-up of itinerant electrons around the W dopant, $3,10$ when doping W^{6+} substitutional with V^{4+} . This provides a chance to incorporate Na ions as the charge compensation reagent, just like the effects of 75 alkali metal ions for rare earth doped phosphor system.⁹ While W as substitutional dopants replaces the V sublattice, the Na ions as interstitial impurity are mainly distributed around W dopant in $Na₂WO₄$ doped $VO₂$. It is reported that the local structure of W dopants have an symmetric tetragonal-like structure, which lead ⁸⁰to locally nucleate rutile-like regions giving rise to the reduction of the thermal activation energy of MIT.^{15,16} In our case, Na ions

around W dopants might expand the scope of rutile-like regions

Physical Chemistry Chemical Physics Accepted Manuscript Physical Chemistry Chemical Physics Accepted Manuscript

in the host matrix and introduce more crystal defects^{16,17}. Therefore, the T_c is even more lowered by ancillary effect of doping with Na.

In summary, we have successfully synthesized W-doped $VO₂$

- s by reduction of doped V_2O_5 using Na_2WO_4 as a full dopant. Under the presence of Na, an impressive depression of the phase transition temperature (about $\sim 32^{\circ}$ C per at% of tungsten dopant using) has been obtained. We have observed that Na has synergic effect on the MIT behaviour for W doped $VO₂$. It is instructive
- 10 and meaningful for improving the preparation technologies of low temperature thermochromic materials and understanding the mechanism of the reduction of critical temperature triggered by doping for $VO₂$ metal-insulator transition. Further work will focus on the detail mechanism and development of new co-
- ¹⁵doping system of alkalis and other dopants.

Financial support is gratefully acknowledged from the National Natural Science Foundation of China (51003009, 21276046 and 21076041), National High Technology Research and

²⁰Development Program of China (863 Program, no. 2008AA03Z306) and the Fundamental Research Funds for the Central Universities of China (DUT11LK16). The Ministry of Education Science and technology research projects and High-Tech R&D projects in Magnesium Industry of Liaoning Province ²⁵in China.

Notes and references

a State Key Laboratory of Fine Chemicals and Faculty of Chemical, Environmental & Biological Science and Technology, Dalian University of Technology,*2 Linggong Road, High Technology Zone, Dalian*

³⁰*116012, P. R. China. Fax: +86-411-84986067; Tel: +86-411-84986067; E-mail: ninggl@dlut.edu.cn*

† Electronic Supplementary Information (ESI) available: Supplemental data of powder X-ray diffraction pattern, differential scanning calorimetry curves and electron microscopy images. See DOI: 10.1039/b000000x/

- 35
	- 1 F. J. Morin, *Phys. Rev. Lett.* 1959, **3**, 34-36; M. Imada, A. Fujimori and Y. Tokura, *Rev. Mod. Phys.*, 1998, **70**, 1039-1263.
- 2 Chudnovskiy, F.; Luryi, S. Spivak and B. Zaslavsky, A. *Ed. Wiley-Interscience: New York*, 2002; 148-155.; D. M. Newns, J. A.
- ⁴⁰Misewich, C. C. Tsuei, A. Gupta, B. A. Scott,and A. Schrott, *Appl. Phys. Lett.* 1998, **73**, 780-782. 4; J. Jeong, N. Aetukuri, T. Graf, T. D. Schladt, M. G. Samant, S. S. P. Parkin, *Science*, 2013, **339**, 1402- 1405.
- 3 L. Whittaker, C. J. Patridge and S. Banerjee, *J. Phys. Chem. Lett.* ⁴⁵2011, **2**, 745-758; T. L. Wu, L. Whittaker, S. Banerjee and G. Sambandamurthy, *Phys. Rev. B* 2011, **83**, 073101; C. Si, W. Xu, H. Wang, J. Zhou, A. Ablat, L. Zhang, J. Cheng, Z. Pan, L. Fan, C. Zou, and Z.Wu Phys. *Chem. Chem. Phys.*, 2012, **14**, 15021-15028.
- 4 C.Tang, P. Georgopoulos, M. E. Fine and J. B.Cohen, *Phys. Rev. B* ⁵⁰1985. **31**, 1000–1011.
- 5 J. Qi, G. L. Ning and Y. Lin, *Mater Res. Bull,* 2008, **43**: 2300-2307; J. W. Ye, L. Zhou, F. J. Liu J. Qi,; W. T. Gong, Y. Lin,and G. L. Ning, *Journal of Alloys and Compounds,* 2010, *504*, 503-507.
- 6 L. Whittaker, T.-L. Wu, C. J. Patridge, S. Ganapathy and S. Banerjee, ⁵⁵*J. Mater. Chem.* 2011, **21**, 5580-5592; Z. Peng, W. Jiang and H. Liu, *J. Phys. Chem. C* 2007, **111**, 1119-1122.
- 7 R. Long, B. Y. Qu, R. C. Tan, Y. F. Sun, X. G. Tan, W. Ying, B. C. Pan, Y. J. Xiong and Y. Xie, *Phys. Chem. Chem. Phys.,* 2012, **14**, 7225–7228; C. Si, W. Xu, H. Wang, J, Zhou, A, Ablat, L. Zhang,
- ⁶⁰J. Cheng, Z. Pan, L. Fan, C. Zouc and Z. Wu, *Phys. Chem. Chem. Phys.*, 2012, **14**, 15021–15028.
- 8 M. Soltani, M. Chaker, E. Haddad, R. Kruzelecky and J. Margot, *Appl. Phys. Lett.* 2004, **85**, 1958-1960.
- 9 W. Burkhardt, T. Christmann, S. Franke, W. Kriegseis, D. Meister, ⁶⁵B. Meyer, W. Niessner, D. Schalch and A. Scharmann, *Thin Solid*
- *Films* 2002, **402**, 226-231; J. Z. Yan, Y. Zhang, W. X. Huang and M. J. Tu, *Thin Solid Films* 2008, **516**, 8554-8558. 10 Z. Zhou, T Komori, N. Matsunami, A. Koizumi and Y Takeda, *Appl*
- *Phys Lett*, 2005, **86**,041107; K. Hayashi, M. Hirano, S. Matsuishi and ⁷⁰H. Hosono, *J. Am. Chem. Soc*, 2002, **124**, 738; J. Liu, H. Z. Lian and C. S. Shi, *Optical Material*, 2007, **29** 1591.
	- 11 B. S. Guiton, Q. Gu,; A. L. Prieto, M. S. Gudiksen and H. Park, *J. Am. Chem. Soc.* 2005, **12**, 498-499; L. Whittaker, C. Jaye, Z. Fu, D. A. Fischer and S. Banerjee, *J. Am. Chem. Soc.* 2009, **131**, 8884– 8894.
	- 12 Z. T. Zhang, Y. F. Gao, Z. Chen, J. Du, C. X. Cao, L. T. Kang and H. J. Luo, *Langmuir,* 2010, **26**, 10738–10744.
- 13 R. Lopez, L. A. Boatner, T. E. Haynes, L. C. Feldman and R. F. Haglund, *J. Appl. Phys.* 2002, **92**, 4031-4037. 24 T. D. Manning, I.
- P. Parkin, R. J. H. Clark, D. Sheel, M. E. Pemble and D. Vernadou, *J. Mater. Chem.* 2002, **12**, 2936-2939.
- 14 T. Yamauchi, M. Isobe and Y. Ueda, *Solid. State. Sci.* 2005, **7**, 874- 881; C. J. Patridge, T. L. Wu, C. Jaye, B. Ravel, E. S. Takeuchi, D. A. Fischer, G. Sambandamurthy and S. Banerjee, *Nano. Lett.* 2010, ⁸⁵**10**, 2448-2453
- 15 X. G. Tan, T. Yao, R. Long, Z. H. Sun, Y. J. Feng,; H. Cheng, X. Yuan, Z W. Q. hang, Q. H. Liu, C. Z. Wu, Y. Xie and S. Q. Wei, *Scientific Reports.* 2012. 2.**466** DOI:doi:10.1038/srep00466
- 16 C. J. Patridge, L. Whittaker, B. Ravel and S. Banerjee, *J. Phys. Chem. C*, 2012, **116**, 3728–3736.
17 K L Holman T M McOueen
- 17 K. L. Holman, T. M. McQueen, A. J. Williams, T. Klimczuk, P. W. H. Stephens, W. Zandbergen, Q. Xu, F. Ronning and R. J. Cava, *Phys. Rev. B,* 2009, **79**, 245114.